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# 2SC5480

Silicon NPN Triple Diffused  
Horizontal Deflection Output

# HITACHI

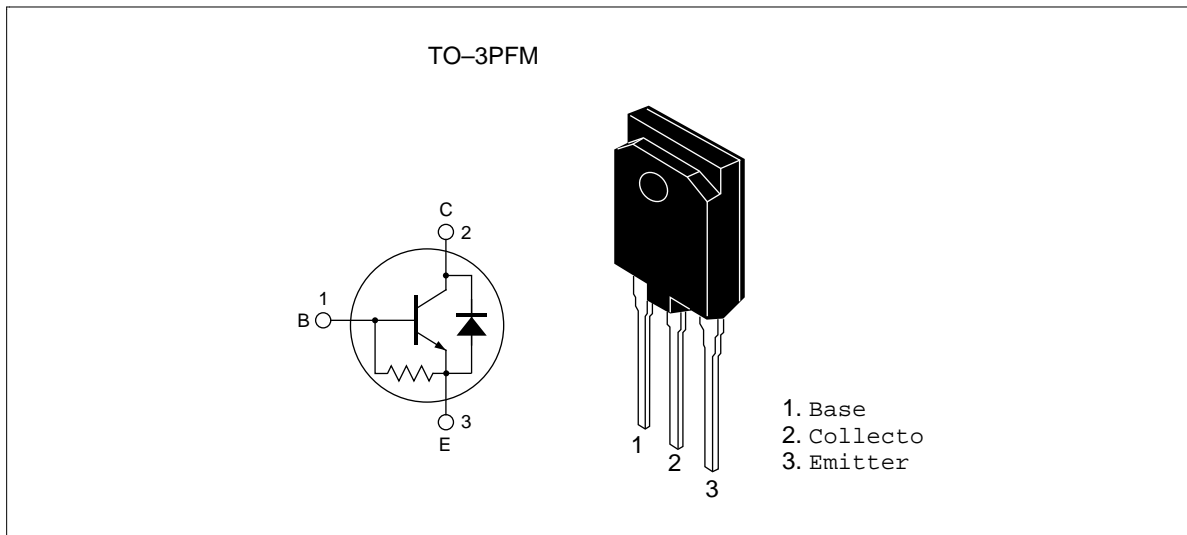
ADE-208-632 (Z)  
1st. Edition  
Oct. 1, 1998

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## Features

- High breakdown voltage  
 $V_{CES} = 1500 \text{ V}$
- Isolated package  
TO-3PFM
- Built-in damper diode

## Outline



## 2SC5480

### Absolute Maximum Ratings (Ta = 25°C)

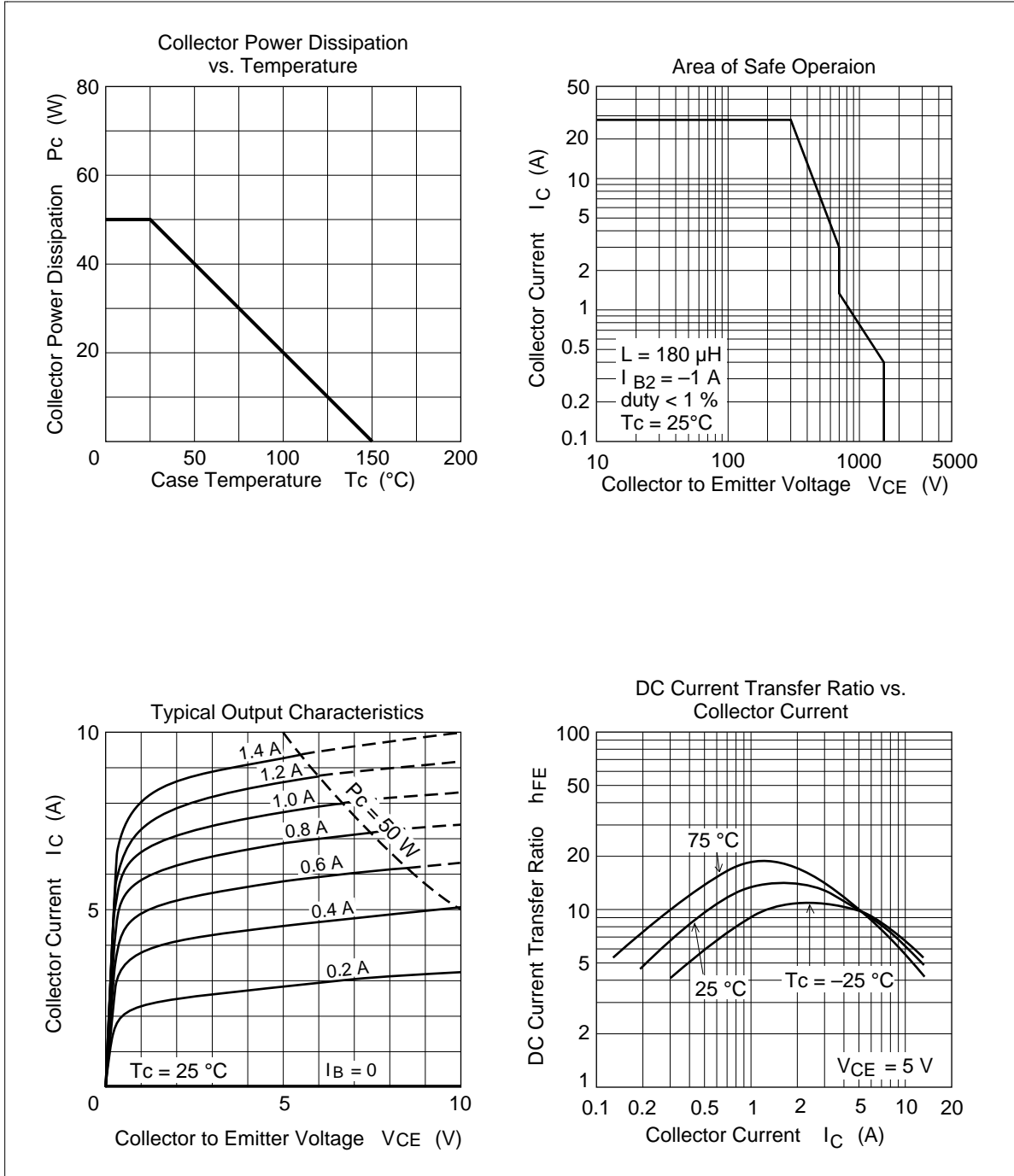
Item	Symbol	Ratings	Unit
Collector to emitter voltage	$V_{CES}$	1500	V
Emitter to base voltage	$V_{EBO}$	5	V
Collector current	$I_C$	14	A
Collector peak current	$i_{c(peak)}$	28	A
Collector power dissipation	$P_C$ <sup>Note1</sup>	50	W
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C
Collector to emitter diode forward current	$I_D$	14	A

Note: 1. Value at  $T_C = 25^\circ\text{C}$

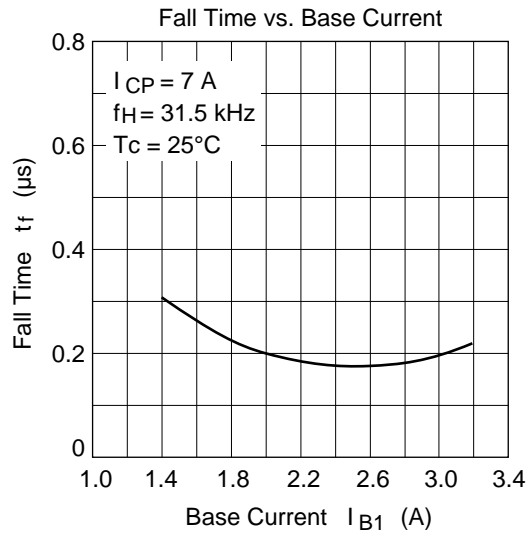
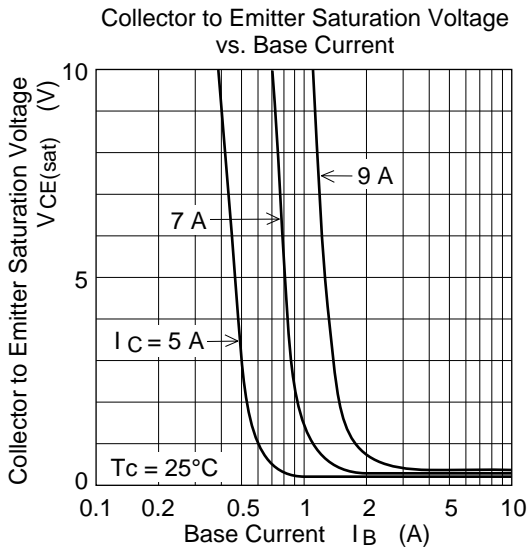
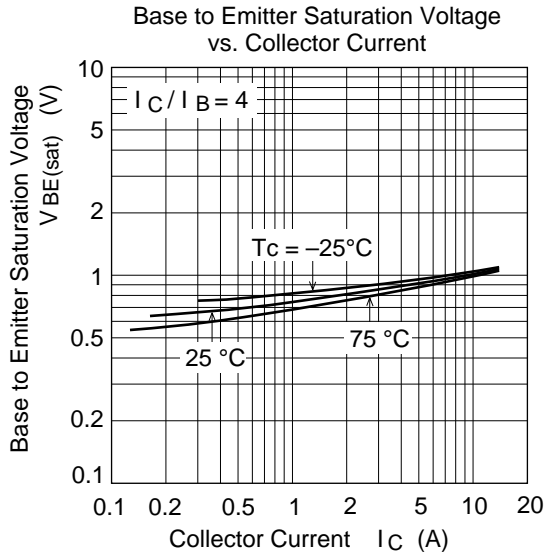
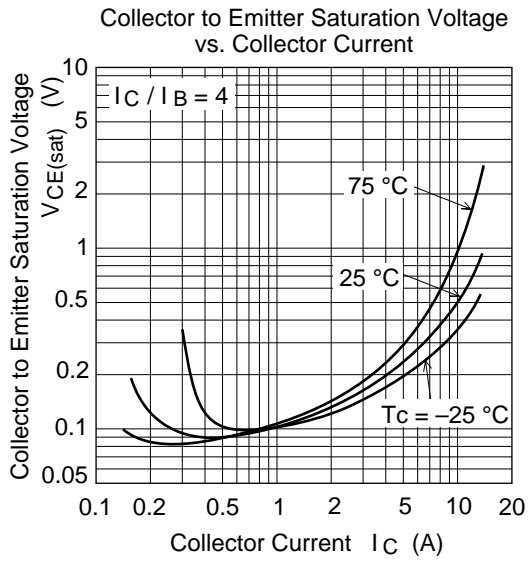
### Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	V	$I_E = 500\text{mA}, I_C = 0$
Collector cutoff current	$I_{CES}$	—	—	500	$\mu\text{A}$	$V_{CE} = 1500\text{V}, R_{BE} = 0$
DC current transfer ratio	$h_{FE1}$	5	—	25		$V_{CE} = 5\text{V}, I_C = 1\text{A}$
DC current transfer ratio	$h_{FE2}$	4	—	7		$V_{CE} = 5\text{V}, I_C = 10\text{A}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	5	V	$I_C = 10\text{A}, I_B = 2.5\text{A}$
Base to emitter saturation voltage	$V_{BE(sat)}$	—	—	1.5	V	$I_C = 10\text{A}, I_B = 2.5\text{A}$
Collector to emitter diode forward voltage	$V_{ECF}$	—	—	2	V	$I_F = 14\text{A}$
Fall time	$t_f$	—	0.2	0.4	$\mu\text{s}$	$I_{CP} = 7\text{A}, I_{B1} = 2.4\text{A}$ $f_H = 31.5\text{kHz}$

Main Characteristics

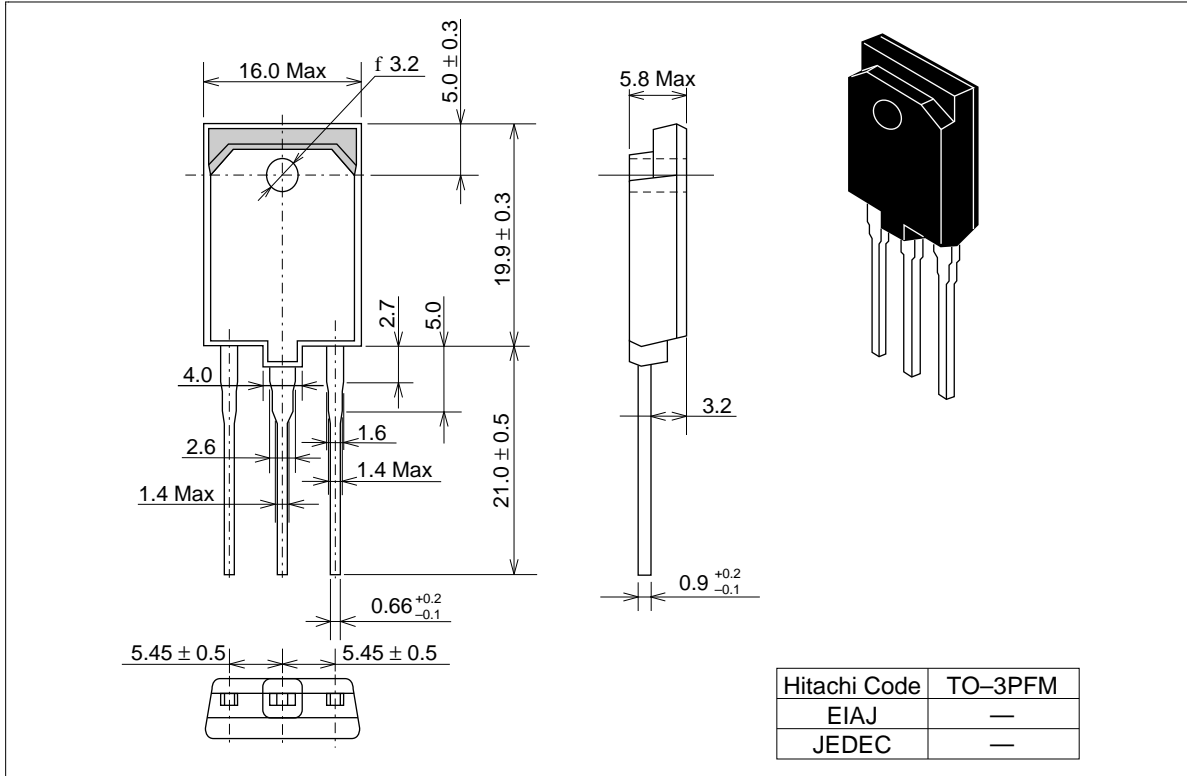


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**2SC5480**

**Package Dimensions (Unit: mm)**



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